

GaN-based UV photodiode

Model GS-ABC-3535MI

General Features:

- UVA+UVB+UVC photodiode
- Photovoltaic mode operation
- SMD 3535 ceramic inorganic package
- Good visible blindness
- High responsivity and low dark current

Applications: air purification, water quality measurement

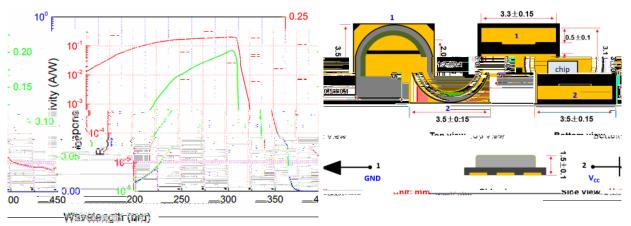




Parameters	Symbol	Value	Unit
Maximum ratings			
Operation temperature range	T _{opt}	-25-85	°C
Storage temperature range	T_{sto}	-40-85	°C
Soldering temperature (3 s)	T _{sol}	260	°C
Reverse voltage	V_{r-max}	-10	V
General characteristics (25 °C)			
Chip size	А	0.22	mm²
Dark current (V _r = -1 V)	l _d	<1	nA
Temperature coefficient (@265 nm)	T _c	0.05	%/°C
Capacitance (at 0 V and 1 MHz)	Cp	3.4	pF
Spectral response characteristics (25 °C)			
Wavelength of peak responsivity	p	355	nm
Peak responsivity (at 355 nm)	R _{max}	0.20	A/W
Spectral response range (R=0.1×R _{max})	-	210-370	nm
UV-visible rejection ratio (R _{max} /R _{400 nm})	-	>10 ⁴	-

Spectral response

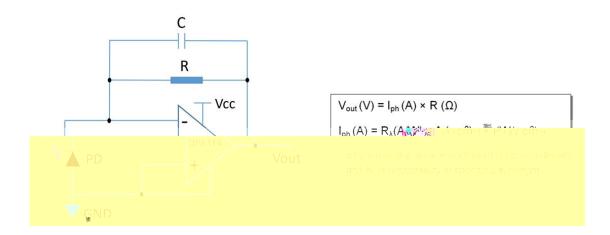
Package dimensions



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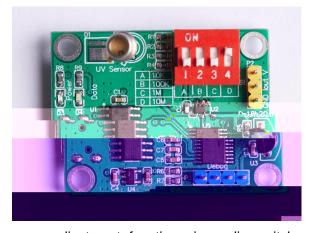
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Application circuit:



Evaluation circuit board:

A small multifunctional amplifier board for developers to simplify and support application development can be separately provided. The evaluation board with one amplifier channel supports both SMD- and TO-type packaged UV photodiodes supplied by GaNo Opto. Users could select one of the two mounting ports for UV photodiode evaluation, while both ports should not be used at the same time.



The evaluation board supports measurement range adjustment function via a dip switch.